Claim 6,	line 7, after "is" insert --formed--;
	line 8, after "is" insert --formed--;
	line 9, after "is" insert --formed--;
	line 11, delete "of"; same line, delete "as".
Claim 7,	line 8, delete "of"; same line, delete "as".
Claim 8,	line 5, delete "to be";
	line 7, delete "to be".

REMARKS

The abstract of the disclosure and specification have been amended to correct errors of a typographical and grammatical nature.

The claims have also been amended to more clearly describe the features of the present invention.

Entry of the preliminary amendments and examination of the application is respectfully requested.

To the extent necessary, Applicant(s) petitions for an extension of time under 37 CFR §1.136. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to the Deposit Account of Antonelli, Terry, Stout & Kraus, LLP

Account No. 01-2135 (501.36951X00) and please credit any overpayment

of fees to such deposit account.

Respectfully submitted,

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ABSTRACT

A reliable semiconductor device is provided with a layered interconnect structure that may develop no problem of voids and interconnect breakdowns, in which the layered interconnect structure includes a conductor film and a neighboring film so layered on a semiconductor substrate that the neighboring film is in contact with the conductor film. In the device, the materials for the conductor film and the neighboring film are so selected that the difference between the short side, a_p, of the rectangular unit cells that constitute the plane with minimum free energy of the conductor film and the short side, a_n, of the rectangular unit cells that constitute the plane with minimum free energy of the neighboring film, $\{ | a_p - a_n | / a_p \} \times 100 = A$ (%) and the difference between the long side, b_p, of the rectangular unit cells that constitute the plane with minimum free energy of the conductor film and the long side, b_n, of the rectangular unit cells that constitute the plane with minimum free energy of the neighboring film, $\{ | b_p - b_n | / b_p \} \times 100 = B$ (%) satisfy an inequality of $\{ A + B \times (a_p / b_p) \} < 13$. In this way, the diffusion of the conductor film is retarded.

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